Trench MOS Barrier Schottky Rectifier

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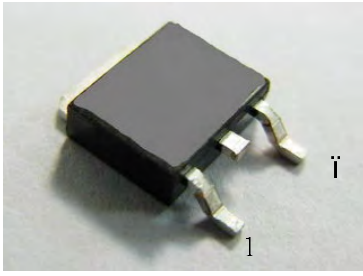

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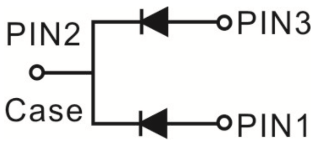


Features

- Advanced trench technology
- Low forward voltage drop
- Low power losses
- High efficiency operation
- Lead Free Finish, RoHS Compliant

Applications

- DC/DC Converters
- AC/DC Adaptors
- Switching Power Supplies
- Freewheeling Diodes

Maximum ratings and electrical characteristics (T_J = 25°C unless otherwise noted)

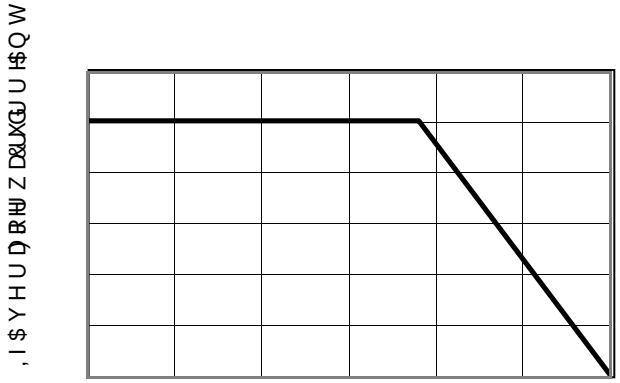
Parameter			Symbol	Limit		Unit
Maximum repetitive peak reverse voltage	per diode		VRRM	0. ЛrÄ ů		
Peak forward surge current 8.3 ms single half sine- wave superimposed on rated load per diode			IFSM	1 0		A
Operating junction and storage temperature range			TJ, TSTG	W R		°C
Typical thermal resistance per leg	TO-2		RΘJC			°C/W
Instantaneous forward voltage per diode			VF(1)	TYP.	MAX.	V
	IF= A	TJ=25°C		0.7	0.7	
	IF= A	TJ=125°C		0.6	-	
	IF=5A	TJ=25°C		0.8	0.	
	IF=5A	TJ=125°C		0.	-	
Instantaneous reverse current per diode at rated reverse voltage	TJ=25°C		IR(2)	1		uA
	TJ=125°C					XA

Notes:

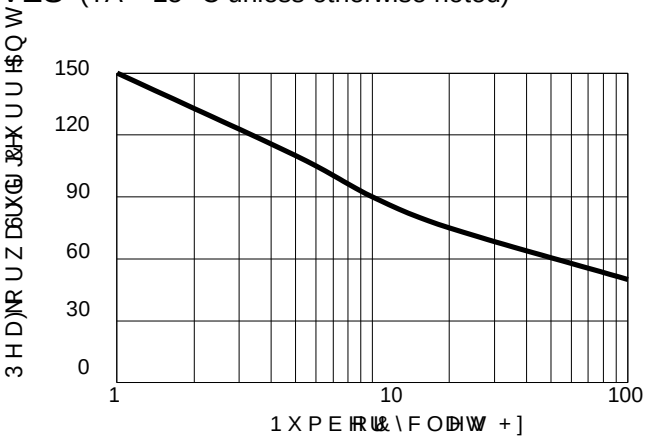
(1) Pulse test: 300 μs pulse width, 1 % duty cycle

(2) Pulse test: Pulse width 0 4 0 ms

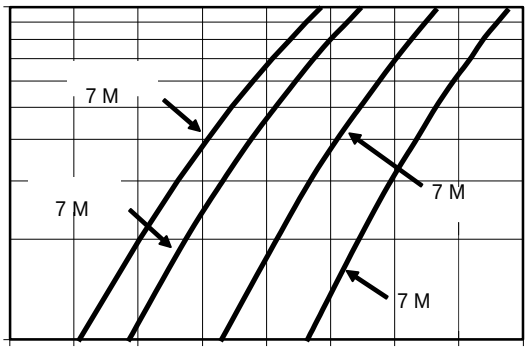
RATINGS AND CHARACTERISTICS CURVES (TA = 25 °C unless otherwise noted)



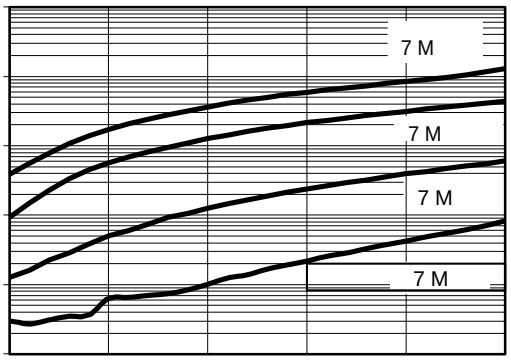
Current Derating, Case



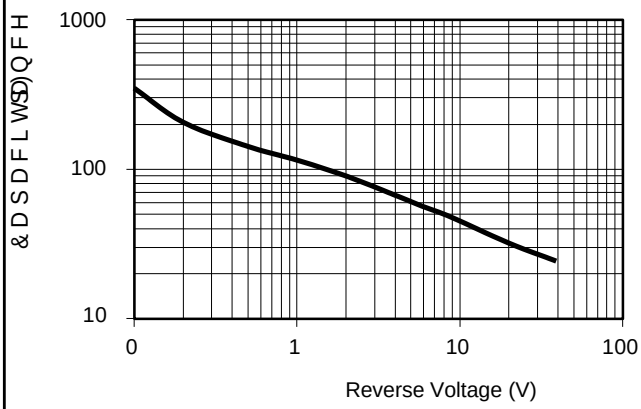
Maximum Repetitive Surge Current



Typical Forward Voltage



Typical Reverse Current



Typical Junction Capacitance

PACKAGE OUTLINE DIMENSIONS

Note:unit In(mm)

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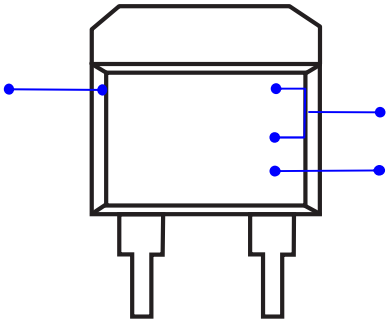

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93'& LQIRUPDWLRQ